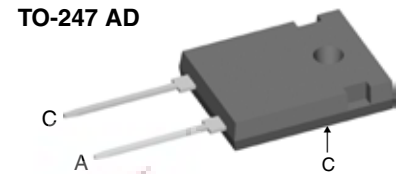
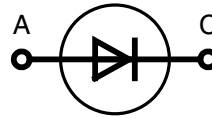


Fast Recovery Epitaxial Diode (FRED)

$I_{FAV} = 37\text{ A}$
 $V_{RRM} = 600\text{ V}$
 $t_{rr} = 35\text{ ns}$

V_{RSM}	V_{RRM}	Type
V	V	
640	600	DSEI 30-06A



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	70	A
I_{FAVM} ①	$T_C = 85^\circ\text{C}$; rectangular, $d = 0.5$	37	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	300	A
		$t = 8.3\text{ ms}$ (60 Hz), sine	320
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	260	A
		$t = 8.3\text{ ms}$ (60 Hz), sine	280
I^2t	$T_{VJ} = 45^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	450	A ² s
		$t = 8.3\text{ ms}$ (60 Hz), sine	420
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	340	A ² s
		$t = 8.3\text{ ms}$ (60 Hz), sine	320
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+150	°C
P_{tot}	$T_C = 25^\circ\text{C}$	125	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Features

- International standard package JEDEC TO-247 AD
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

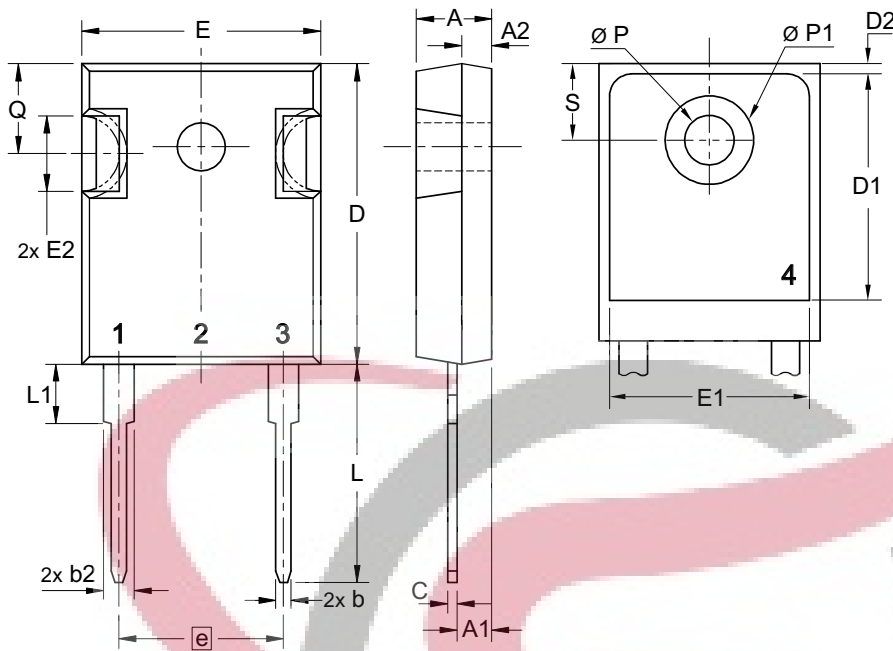
Symbol	Conditions	Characteristic Values		
		typ.	max.	
I_R	$V_R = V_{RRM}$ $V_R = 0.8 \cdot V_{RRM}$ $V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	100	µA
		$T_{VJ} = 25^\circ\text{C}$	50	µA
		$T_{VJ} = 125^\circ\text{C}$	7	mA
V_F	$I_F = 37\text{ A}$	$T_{VJ} = 150^\circ\text{C}$	1.4	V
		$T_{VJ} = 25^\circ\text{C}$	1.6	V
V_{T0}	For power-loss calculations only		1.01	V
r_T	$T_{VJ} = T_{VJM}$		7.1	mΩ
R_{thJC}			1	K/W
R_{thCH}		0.25		K/W
t_{rr}	$I_F = 1\text{ A}$; $-di/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$; $T_{VJ} = 25^\circ\text{C}$	35	50	ns
I_{RM}	$V_R = 350\text{ V}$; $I_F = 30\text{ A}$; $-di_F/dt = 240\text{ A}/\mu\text{s}$ $L \leq 0.05\text{ }\mu\text{H}$; $T_{VJ} = 100^\circ\text{C}$	10	11	A

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} . $V_R = 0.8 \cdot V_{RRM}$, duty cycle $d = 0.5$
Data according to IEC 60747

Dimensions TO-247 AD



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

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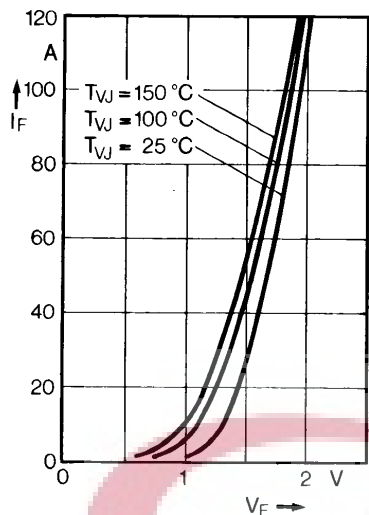


Fig. 1 Forward current versus voltage drop

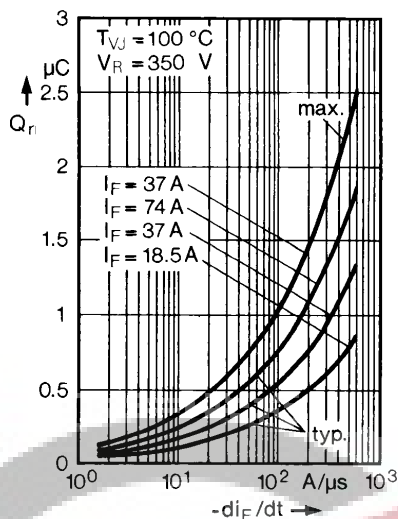


Fig. 2 Recovery charge versus $-di_F/dt$

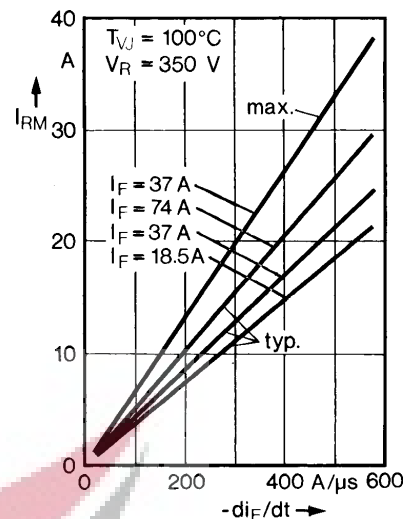


Fig. 3 Peak reverse current versus $-di_F/dt$

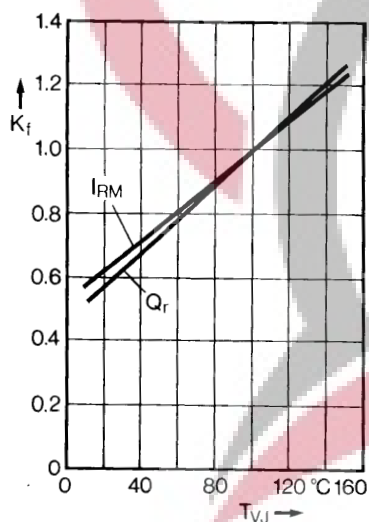


Fig. 4 Dynamic parameters vs. junction temperature

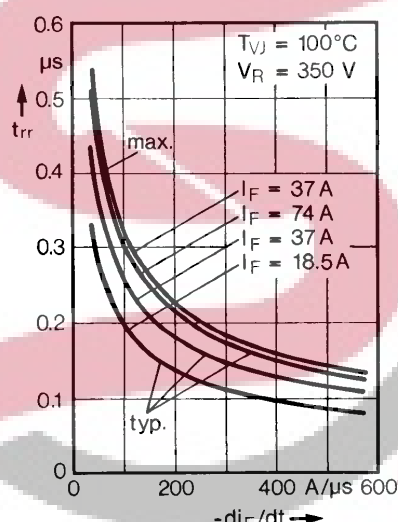


Fig. 5 Recovery time versus $-di_F/dt$

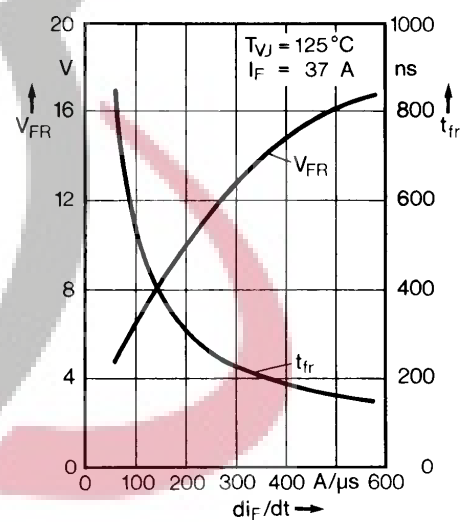


Fig. 6 Peak forward voltage versus di_F/dt

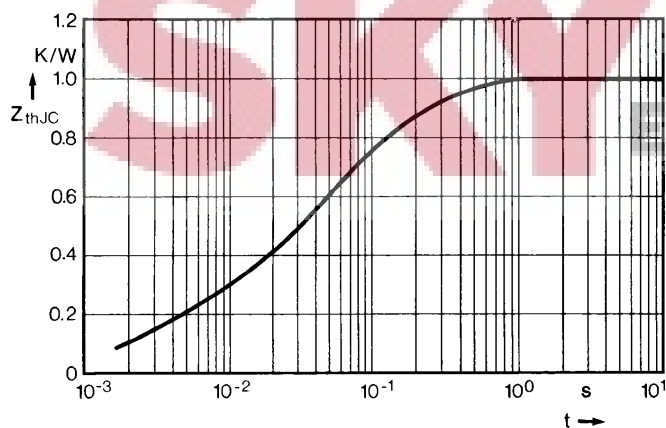


Fig. 7 Transient thermal impedance junction to case

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